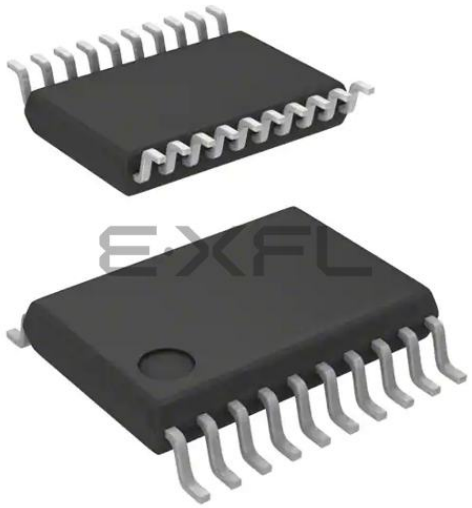
Renesas Electronics America Inc - R5F21174SP#U0 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, SIO, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	13
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 4x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21174sp-u0

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1. Overview

This MCU is built using the high-performance silicon gate CMOS process using the R8C/Tiny Series CPU core and is packaged in a 20-pin plastic molded LSSOP. This MCU operates using sophisticated instructions featuring a high level of instruction efficiency. With 1 Mbyte of address space, it is capable of executing instructions at high speed.
Furthermore, the data flash ROM (1KB × 2blocks) is embedded in the R8C/17 group.
The difference between the R8C/16 and R8C/17 groups is only the existence of the data flash ROM. Their peripheral functions are the same.

1.1 Applications

Electric household appliance, office equipment, housing equipment (sensor, security), general industrial equipment, audio, etc.

Table 1.2 Performance Outline of the R8C/17 Group

Item		Performance
CPU	Number of Basic Instructions	89 instructions
	Minimum Instruction Execution Time	50ns(f(XIN)=20MHz, VCC=3.0 to 5.5V) 100ns(f(XIN)=10MHz, VCC=2.7 to 5.5V)
	Operating Mode	Single-chip
	Address Space	1 Mbyte
	Memory Capacity	See **Table 1.4 R8C/17 Group Product Information**
Peripheral Function	Port	I/O : 13 pins (including LED drive port), Input : 2 pin
	LED drive port	I/O port: 4 pins
	Timer	Timer X: 8 bits × 1 channel, Timer Z: 8 bits × 1 channel (Each timer equipped with 8-bit prescaler) Timer C: 16 bits × 1 channel (Circuits of input capture and output compare)
	Serial Interface	1 channel Clock synchronous serial I/O, UART
	I^2C bus Interface (IIC)(1)	1 channel
	A/D Converter	10-bit A/D converter: 1 circuit, 4 channels
	Watchdog Timer	15 bits × 1 channel (with prescaler) Reset start selectable, Count source protection mode
	Interrupt	Internal: 9 factors, External: 4 factors, Software: 4 factors Priority level: 7 levels
	Clock Generation Circuit	2 circuits Main clock generation circuit (Equipped with a built-in feedback resistor) On-chip oscillator (high speed, low speed) Equipped with frequency adjustment function on high-speed on-chip oscillator
	Oscillation Stop Detection Function	Main clock oscillation stop detection function
	Voltage Detection Circuit	Included
	Power-on Reset Circuit	Included
Electric Characteristics	Supply Voltage	VCC=3.0 to 5.5V (f(XIN)=20MHz) VCC=2.7 to 5.5V (f(XIN)=10MHz)
	Power Consumption	Typ. 9mA (VCC = 5.0V, f(XIN) = 20MHz) Typ. 5mA (VCC = 3.0V, f(XIN) = 10MHz) Typ.35μA (VCC = 3.0V, wait mode, peripheral clock off) Typ. 0.7μA (VCC = 3.0V, stop mode)
Flash Memory	Program/Erase Supply Voltage	VCC=2.7 to 5.5V
	Program and Erase Endurance	10,000 times (Data flash) 1,000 times (Program ROM)
Operating Ambient Temperature		-20 to 85°C -40 to 85°C (D Version)
Package		20-pin plastic mold LSSOP

NOTES:

1. I^2C bus is a trademark of Koninklijke Philips Electronics N. V.

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.

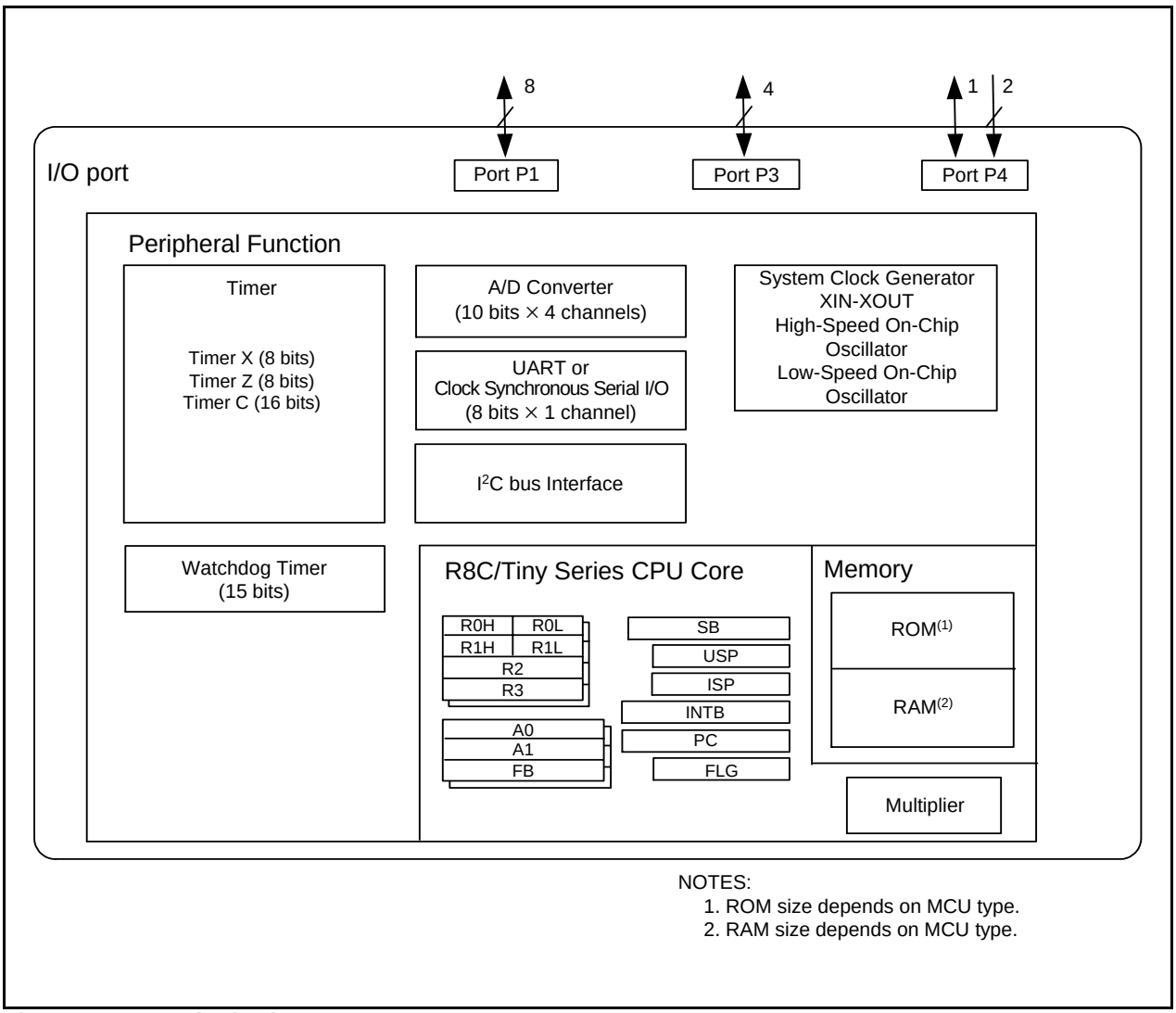


Figure 1.1 Block Diagram

1.4 Product Information

Table 1.3 lists the Product Information of R8C/16 Group and Table 1.4 lists the Product Information of R8C/17 Group.

Table 1.3 Product Information of R8C/16 Group **As of Jan 2006**

Type No.	ROM Capacity	RAM Capacity	Package Type	Remarks
R5F21162SP	8 Kbytes	512 bytes	PLSP0020JB-A	Flash Memory Version
R5F21163SP	12 Kbytes	768 bytes	PLSP0020JB-A	
R5F21164SP	16 Kbytes	1 Kbyte	PLSP0020JB-A	
R5F21162DSP	8 Kbytes	512 bytes	PLSP0020JB-A	D Version
R5F21163DSP	12 Kbytes	768 bytes	PLSP0020JB-A	
R5F21164DSP	16 Kbytes	1 Kbyte	PLSP0020JB-A	

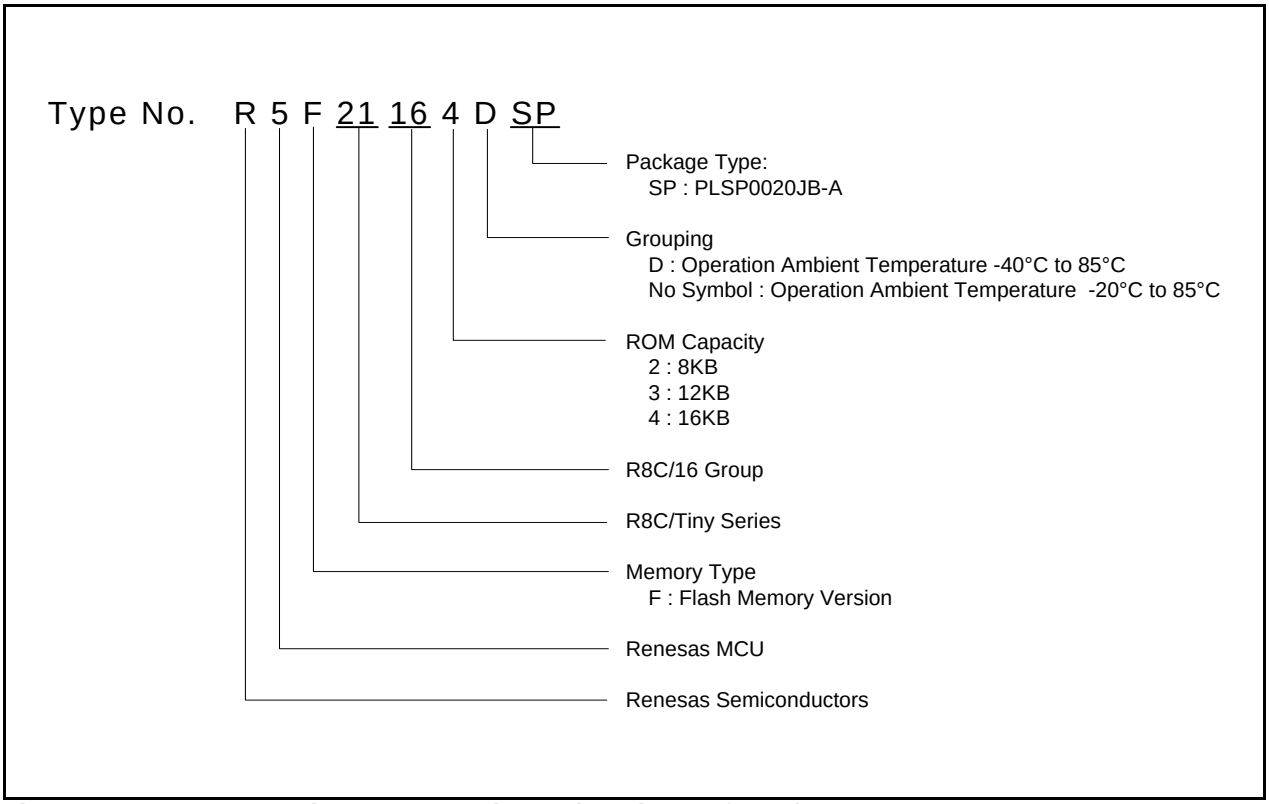


Figure 1.2 Part Number, Memory Size and Package of R8C/16 Group

Table 1.4 Product Information of R8C/17 Group **As of Jan 2006**

Type No.	ROM Capacity		RAM Capacity	Package Type	Remarks
	Program ROM	Data flash			
R5F21172SP	8 Kbytes	1 Kbyte × 2	512 bytes	PLSP0020JB-A	Flash Memory Version
R5F21173SP	12 Kbytes	1 Kbyte × 2	768 bytes	PLSP0020JB-A	
R5F21174SP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A	
R5F21172DSP	8 Kbytes	1 Kbyte × 2	512 bytes	PLSP0020JB-A	D Version
R5F21173DSP	12 Kbytes	1 Kbyte × 2	768 bytes	PLSP0020JB-A	
R5F21174DSP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLSP0020JB-A	

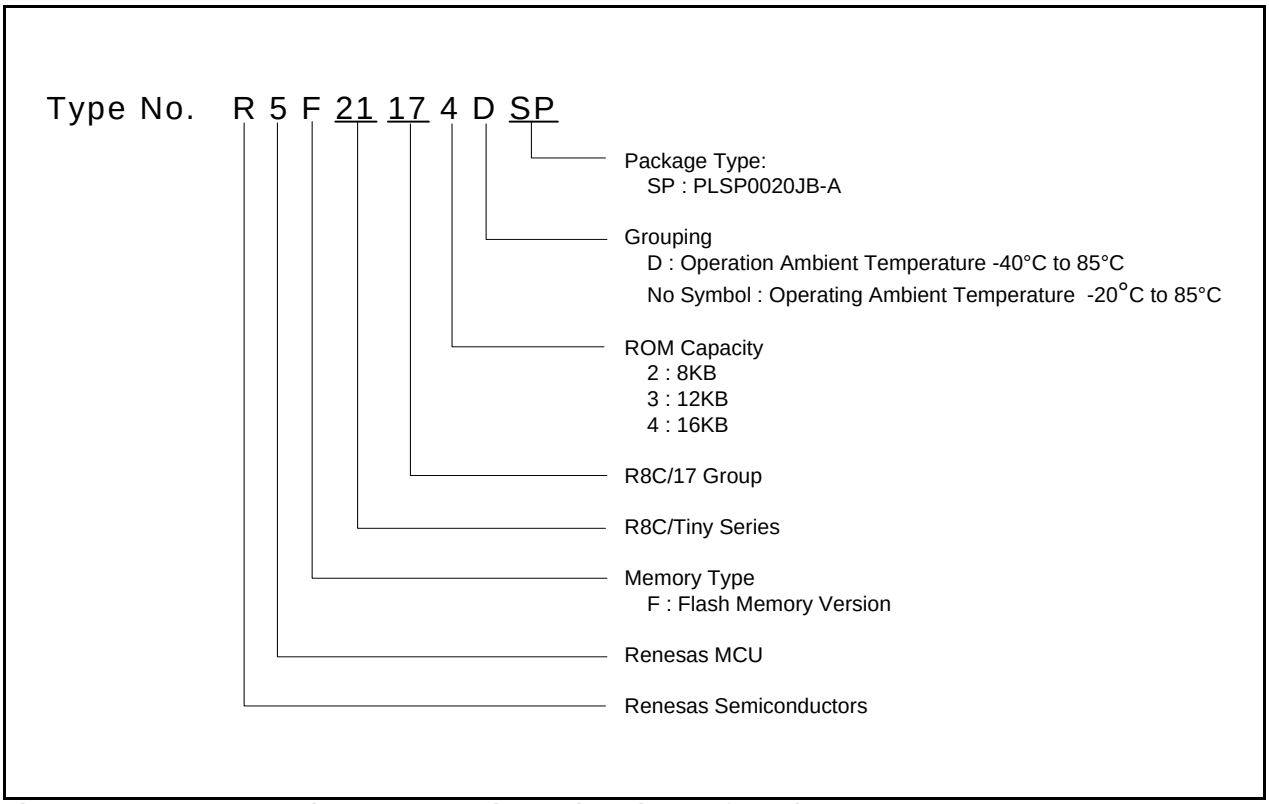


Figure 1.3 Part Number, Memory Size and Package of R8C/17 Group

1.6 Pin Description

Table 1.5 lists the Pin Description and Table 1.6 lists the Pin Name Information by Pin Number.

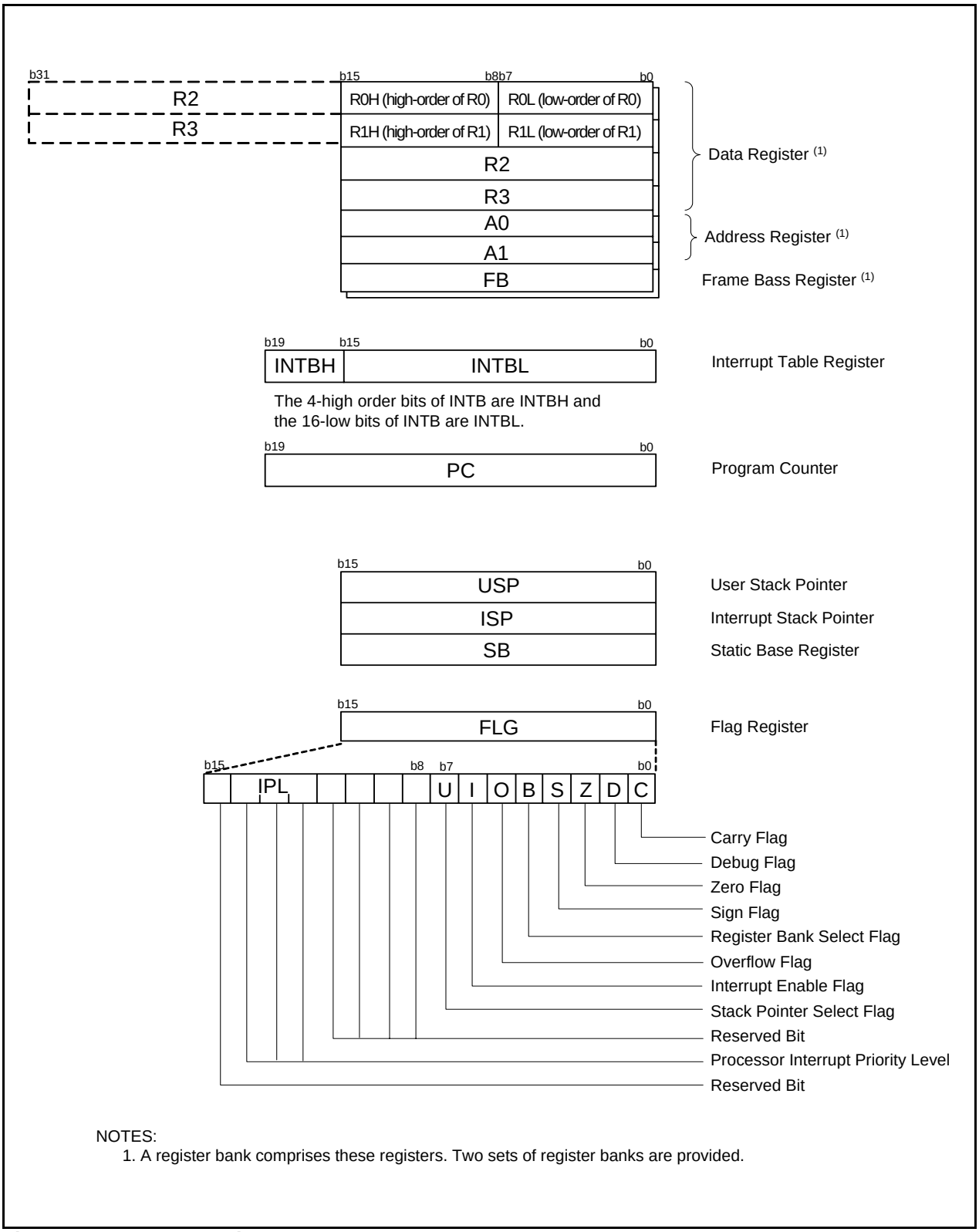
Table 1.5 Pin Description

Function	Pin Name	I/O Type	Description
Power Supply Input	VCC VSS	I	Apply 2.7V to 5.5V to the VCC pin. Apply 0V to the VSS pin
Analog Power Supply Input	AVCC AVSS	I	Power supply input pins to A/D converter. Connect AVCC to VCC. Apply 0V to AVSS. Connect a capacitor between AVCC and AVSS.
Reset Input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU
MODE	MODE	I	Connect this pin to VCC via a resistor
Main Clock Input	XIN	I	These pins are provided for the main clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an externally derived clock, input it to the XIN pin and leave the XOUT pin open.
Main Clock Output	XOUT	O	
$\overline{\text{INT}}$ Interrupt	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	INT interrupt input pins
Key Input Interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer X	CNTR0	I/O	Timer X I/O pin
	$\overline{\text{CNTR0}}$	O	Timer X output pin
Timer Z	TZOUT	O	Timer Z output pin
Timer C	TCIN	I	Timer C input pin
	CMP0_0 to CMP0_2, CMP1_0 to CMP1_2	O	Timer C output pins
Serial Interface	CLK0	I/O	Transfer clock I/O pin
	RXD0	I	Serial data input pin
	TXD0	O	Serial data output pin
I^2C bus Interface (IIC)	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Reference Voltage Input	VREF	I	Reference voltage input pin to A/D converter Connect VREF to VCC
A/D Converter	AN8 to AN11	I	Analog input pins to A/D converter
I/O Port	P1_0 to P1_7, P3_3 to P3_5, P3_7, P4_5	I/O	These are CMOS I/O ports. Each port contains an I/O select direction register, allowing each pin in that port to be directed for input or output individually. Any port set to input can select whether to use a pull-up resistor or not by program. P1_0 to P1_3 also function as LED drive ports.
Input Port	P4_6, P4_7	I	Port for input-only

I: Input O: Output I/O: Input and output

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Register. The CPU contains 13 registers. Of these, R0, R1, R2, R3, A0, A1 and FB comprise a register bank. Two sets of register banks are provided.



NOTES:
1. A register bank comprises these registers. Two sets of register banks are provided.

Figure 2.1 CPU Register

2.1 Data Registers (R0, R1, R2 and R3)

R0 is a 16-bit register for transfer, arithmetic and logic operations. The same applies to R1 to R3. The R0 can be split into high-order bit (R0H) and low-order bit (R0L) to be used separately as 8-bit data registers. The same applies to R1H and R1L as R0H and R0L. R2 can be combined with R0 to be used as a 32-bit data register (R2R0). The same applies to R3R1 as R2R0.

2.2 Address Registers (A0 and A1)

A0 is a 16-bit register for address register indirect addressing and address register relative addressing. They also are used for transfer, arithmetic and logic operations. The same applies to A1 as A0. A0 can be combined with A0 to be used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register indicates the start address of an interrupt vector table.

2.5 Program Counter (PC)

PC, 20 bits wide, indicates the address of an instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The stack pointer (SP), USP and ISP, are 16 bits wide each. The U flag of FLG is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register for SB relative addressing.

2.8 Flag Register (FLG)

FLG is a 11-bit register indicating the CPU state.

2.8.1 Carry Flag (C)

The C flag retains a carry, borrow, or shift-out bit that has occurred in the arithmetic logic unit.

2.8.2 Debug Flag (D)

The D flag is for debug only. Set to “0”.

2.8.3 Zero Flag (Z)

The Z flag is set to “1” when an arithmetic operation resulted in 0; otherwise, “0”.

2.8.4 Sign Flag (S)

The S flag is set to “1” when an arithmetic operation resulted in a negative value; otherwise, “0”.

2.8.5 Register Bank Select Flag (B)

The register bank 0 is selected when the B flag is “0”. The register bank 1 is selected when this flag is set to “1”.

2.8.6 Overflow Flag (O)

The O flag is set to “1” when the operation resulted in an overflow; otherwise, “0”.

2.8.7 Interrupt Enable Flag (I)

The I flag enables a maskable interrupt.
An interrupt is disabled when the I flag is set to “0”, and are enabled when the I flag is set to “1”. The I flag is set to “0” when an interrupt request is acknowledged.

2.8.8 Stack Pointer Select Flag (U)

ISP is selected when the U flag is set to “0”, USP is selected when the U flag is set to “1”.
The U flag is set to “0” when a hardware interrupt request is acknowledged or the INT instruction of software interrupt numbers 0 to 31 is executed.

2.8.9 Processor Interrupt Priority Level (IPL)

IPL, 3 bits wide, assigns processor interrupt priority levels from level 0 to level 7.
If a requested interrupt has greater priority than IPL, the interrupt is enabled.

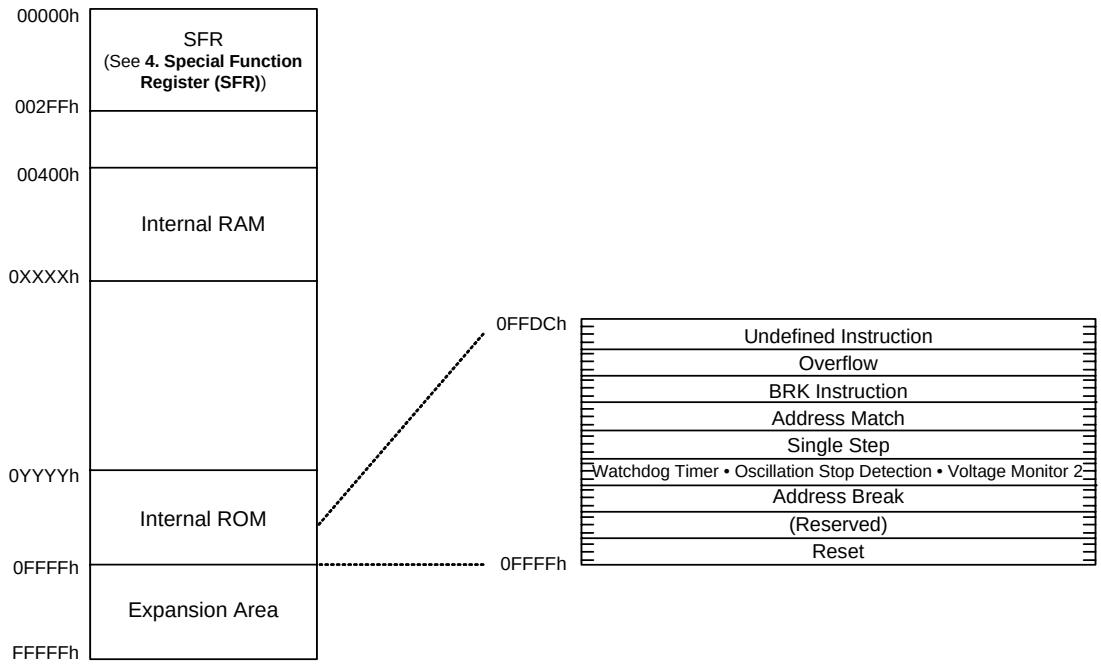
2.8.10 Reserved Bit

When write to this bit, set to “0”. When read, its content is indeterminate.

3. Memory

3.1 R8C/16 Group

Figure 3.1 is a Memory Map of the R8C/16 group. The R8C/16 group provides 1-Mbyte address space from addresses 00000h to FFFFFh.
The internal ROM is allocated lower addresses beginning with address 0FFFFh. For example, a 16-Kbyte internal ROM is allocated addresses 0C000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses beginning with address 00400h. For example, a 1-Kbyte internal RAM is allocated addresses 00400h to 007FFh. The internal RAM is used not only for storing data but for calling subroutines and stacks when interrupt request is acknowledged.
Special function registers (SFR) are allocated addresses 00000h to 002FFh. The peripheral function control registers are allocated them. All addresses, which have nothing allocated within the SFR, are reserved area and cannot be accessed by users.



NOTES:
1. Blank spaces are reserved. No access is allowed.

Part Number	Internal ROM		Internal RAM	
	Size	0YYYYh	Size	0XXXXh
R5F21164SP, R5F21164DSP	16 Kbytes	0C000h	1 Kbyte	007FFh
R5F21163SP, R5F21163DSP	12 Kbytes	0D000h	768 bytes	006FFh
R5F21162SP, R5F21162DSP	8 Kbytes	0E000h	512 bytes	005FFh

Figure 3.1 Memory Map of R8C/16 Group

Table 4.2 SFR Information(2)(1)

Address	Register	Symbol	After reset
0040h			
0041h			
0042h			
0043h			
0044h			
0045h			
0046h			
0047h			
0048h			
0049h			
004Ah			
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	IIC Interrupt Control Register	IIC2AIC	XXXXX000b
0050h	Compare 1 Interrupt Control Register	CMP1IC	XXXXX000b
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h			
0056h	Timer X Interrupt Control Register	TXIC	XXXXX000b
0057h			
0058h	Timer Z Interrupt Control Register	TZIC	XXXXX000b
0059h	$\overline{\text{INT1}}$ Interrupt Control Register	INT1IC	XXXXX000b
005Ah	$\overline{\text{INT3}}$ Interrupt Control Register	INT3IC	XXXXX000b
005Bh	Timer C Interrupt Control Register	TCIC	XXXXX000b
005Ch	Compare 0 Interrupt Control Register	CMP0IC	XXXXX000b
005Dh	$\overline{\text{INT0}}$ Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah			
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h			
0073h			
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

NOTES:

1. Blank spaces are reserved. No access is allowed.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated value	Unit
V_{CC}	Supply Voltage	V_{CC} = AV_{CC}	-0.3 to 6.5	V
AV_{CC}	Analog Supply Voltage	V_{CC} = AV_{CC}	-0.3 to 6.5	V
V_I	Input Voltage		-0.3 to V_{CC}+0.3	V
V_O	Output Voltage		-0.3 to V_{CC}+0.3	V
P_d	Power Dissipation	T_{opr} = 25°C	300	mW
T_{opr}	Operating Ambient Temperature		-20 to 85 / -40 to 85 (D version)	°C
T_{stg}	Storage Temperature		-65 to 150	°C

Table 5.2 Recommended Operating Conditions

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
V_{CC}	Supply Voltage			2.7	–	5.5	V
AV_{CC}	Analog Supply Voltage			–	V_{CC}(3)	–	V
V_{SS}	Supply Voltage			–	0	–	V
AV_{SS}	Analog Supply Voltage			–	0	–	V
V_{IH}	Input “H” Voltage			0.8V_{CC}	–	V_{CC}	V
V_{IL}	Input “L” Voltage			0	–	0.2V_{CC}	V
$I_{OH(sum)}$	Peak Sum Output “H” Current	Sum of All Pins $I_{OH\ (peak)}$		–	–	-60	mA
$I_{OH(peak)}$	Peak Output “H” Current			–	–	-10	mA
$I_{OH(avg)}$	Average Output “H” Current			–	–	-5	mA
$I_{OL(sum)}$	Peak Sum Output “L” Currents	Sum of All Pins $I_{OL\ (peak)}$		–	–	60	mA
$I_{OL(peak)}$	Peak Output “L” Currents	Except P1_0 to P1_3		–	–	10	mA
		P1_0 to P1_3	Drive Capacity HIGH	–	–	30	mA
			Drive Capacity LOW	–	–	10	mA
$I_{OL(avg)}$	Average Output “L” Current	Except P1_0 to P1_3		–	–	5	mA
		P1_0 to P1_3	Drive Capacity HIGH	–	–	15	mA
			Drive Capacity LOW	–	–	5	mA
$f_{(XIN)}$	Main Clock Input Oscillation Frequency		3.0V ≤ V_{CC} ≤ 5.5V	0	–	20	MHz
			2.7V ≤ V_{CC} < 3.0V	0	–	10	MHz

NOTES:
1. V_{CC} = AV_{CC} = 2.7 to 5.5V at T_{opr} = -20 to 85 °C / -40 to 85 °C, unless otherwise specified.
2. The typical values when average output current is 100ms.
3. Hold V_{CC} = AV_{CC}.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/Erase Endurance(2)	R8C/16 Group	100(3)	–	–	times
		R8C/17 Group	1,000(3)	–	–	times
–	Byte Program Time	V_{CC} = 5.0 V at T_{opr} = 25 °C	–	50	400	µs
–	Block Erase Time	V_{CC} = 5.0 V at T_{opr} = 25 °C	–	0.4	9	s
$t_{d(SR-ES)}$	Time Delay from Suspend Request until Erase Suspend		–	–	8	ms
–	Erase Suspend Request Interval		10	–	–	ms
–	Program, Erase Voltage		2.7	–	5.5	V
–	Read Voltage		2.7	–	5.5	V
–	Program, Erase Temperature		0	–	60	°C
–	Data Hold Time(7)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = AVcc = 2.7 to 5.5V at T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of program and erase
   The program and erase endurance shows an erase endurance for every block.
   If the program and erase endurance is “n” times (n = 100, 10000), “n” times erase can be performed for every block.
   For example, if performing 1-byte write to the distinct addresses on Block A of 1Kbyte block 1,024 times and then erasing that block, program and erase endurance is counted as one time.
   However, do not perform multiple programs to the same address for one time ease.(disable overwriting).
3. Endurance to guarantee all electrical characteristics after program and erase.(1 to “Min.” value can be guaranateed).
4. In the case of a system to execute multiple programs, perform one erase after programming as reducing effective reprogram endurance not to leave blank area as possible such as programming write addresses in turn. If programming a set of 16 bytes, programming up to 128 sets and then erasing them one time can reduce effective reprogram endurance. Additionally, averaging erase endurance for Block A and B can reduce effective reprogram endurance more. To leave erase endurance for every block as information and determine the restricted endurance are recommended.
5. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
6. Customers desiring Program/Erase failure rate information should contact their Renesas technical support representative.
7. The data hold time incudes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/Erase Endurance(2)		10,000(3)	–	–	times
–	Byte Program Time (Program/Erase Endurance ≤ 1,000 Times)	V_{CC} = 5.0 V at T_{opr} = 25 °C	–	50	400	µs
	Byte Program Time (Program/Erase Endurance > 1,000 Times)	V_{CC} = 5.0 V at T_{opr} = 25 °C	–	65	–	µs
	Block Erase Time (Program/Erase Endurance ≤ 1,000 Times)	V_{CC} = 5.0 V at T_{opr} = 25 °C	–	0.2	9	s
–	Block Erase Time (Program/Erase Endurance > 1,000 Times)	V_{CC} = 5.0 V at T_{opr} = 25 °C	–	0.3	–	s
$t_{d(SR-ES)}$	Time Delay from Suspend Request until Erase Suspend		–	–	8	ms
–	Erase Suspend Request Interval		10	–	–	ms
–	Program, Erase Voltage		2.7	–	5.5	V
–	Read Voltage		2.7	–	5.5	V
–	Program, Erase Temperature		-20(8)	–	85	°C
–	Data Hold Time(9)	Ambient temperature = 55 °C	20	–	–	year

NOTES:
1. V_{CC} = AVcc = 2.7 to 5.5V at Topr = –20 to 85 °C / –40 to 85 °C, unless otherwise specified.
2. Definition of program and erase
   The program and erase endurance shows an erase endurance for every block.
   If the program and erase endurance is “n” times (n = 100, 10000), “n” times erase can be performed for every block.
   For example, if performing 1-byte write to the distinct addresses on Block A of 1Kbyte block 1,024 times and then erasing that block, program and erase endurance is counted as one time.
   However, do not perform multiple programs to the same address for one time ease.(disable overwriting).
3. Endurance to guarantee all electrical characteristics after program and erase.(1 to “Min.” value can be guaranateed).
4. Standard of Block A and Block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times are the same as that in program area.
5. In the case of a system to execute multiple programs, perform one erase after programming as reducing effective reprogram endurance not to leave blank area as possible such as programming write addresses in turn. If programming a set of 16 bytes, programming up to 128 sets and then erasing them one time can reduce effective reprogram endurance. Additionally, averaging erase endurance for Block A and B can reduce effective reprogram endurance more. To leave erase endurance for every block as information and determine the restricted endurance are recommended.
6. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
7. Customers desiring Program/Erase failure rate information should contact their Renesas technical support representative.
8. -40 °C for D version.
9. The data hold time incudes time that the power supply is off or the clock is not supplied.

Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset)

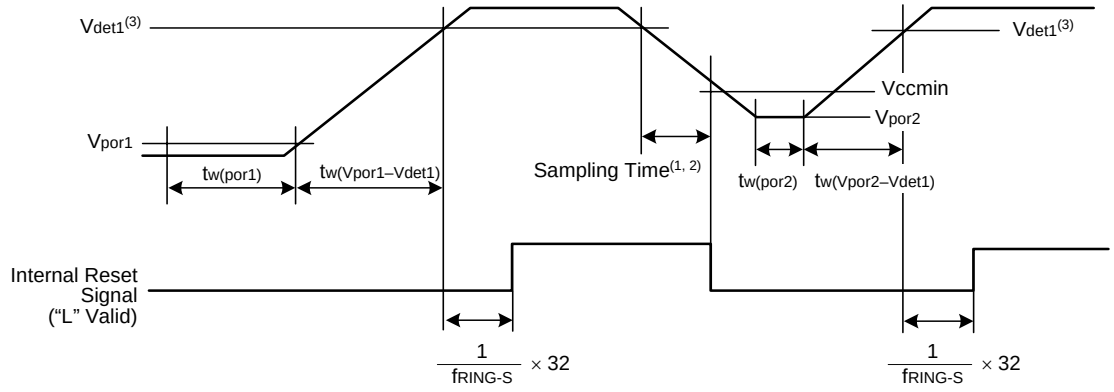
Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por2}	Power-On Reset Valid Voltage	-20°C ≤ Topr < 85°C	–	–	V_{det1}	V
$t_{w(Vpor2-Vdet1)}$	Supply Voltage Rising Time When Power-On Reset is Deasserted(1)	-20°C ≤ Topr < 85°C, $t_{w(por2)}$ ≥ 0s(3)	–	–	100	ms

NOTES:
1. This condition is not applicable when using with Vcc ≥ 1.0V.
2. When turning power on after the time to hold the external power below effective voltage (V_{por1}) exceeds10s, refer to **Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)**.
3. $t_{w(por2)}$ is time to hold the external power below effective voltage (V_{por2}).

Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-On Reset Valid Voltage	-20°C ≤ Topr < 85°C	–	–	0.1	V
$t_{w(Vpor1-Vdet1)}$	Supply Voltage Rising Time When Power-On Reset is Deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 10s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply Voltage Rising Time When Power-On Reset is Deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 30s(2)	–	–	100	ms
$t_{w(Vpor1-Vdet1)}$	Supply Voltage Rising Time When Power-On Reset is Deasserted	-20°C ≤ Topr < 0°C, $t_{w(por1)}$ ≥ 10s(2)	–	–	1	ms
$t_{w(Vpor1-Vdet1)}$	Supply Voltage Rising Time When Power-On Reset is Deasserted	0°C ≤ Topr ≤ 85°C, $t_{w(por1)}$ ≥ 1s(2)	–	–	0.5	ms

NOTES:
1. When not using the voltage monitor 1 reset, use with Vcc≥ 2.7V.
2. $t_{w(por1)}$ is time to hold the external power below effective voltage (V_{por1}).



NOTES:
1. Hold the voltage of the microcomputer operation voltage range (Vccmin or above) within sampling time.
2. A sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det1} indicates the voltage detection level of the voltage detection 1 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.3 Reset Circuit Electrical Characteristics

Table 5.13 Electrical Characteristics (1) [Vcc = 5V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” Voltage	Except X_{OUT}	I_{OH} = -5mA		V_{CC} – 2.0	–	V_{CC}	V
			I_{OH} = -200µA		V_{CC} – 0.3	–	V_{CC}	V
		X_{OUT}	Drive capacity HIGH	I_{OH} = -1mA	V_{CC} – 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500µA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” Voltage	Except P1_0 to P1_3, X_{OUT}	I_{OL} = 5mA		–	–	2.0	V
			I_{OL} = 200µA		–	–	0.45	V
		P1_0 to P1_3	Drive capacity HIGH	I_{OL} = 15mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 5mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 200µA	–	–	0.45	V
		X_{OUT}	Drive capacity HIGH	I_{OL} = 1mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500µA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	1.0	V
		$\overline{RESET}$			0.2	–	2.2	V
I_{IH}	Input “H” current		VI = 5V		–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0V		–	–	-5.0	µA
R_{PULLUP}	Pull-Up Resistance		VI = 0V		30	50	167	kΩ
R_{fXIN}	Feedback Resistance	XIN			–	1.0	–	MΩ
f_{RING-S}	Low-Speed On-Chip Oscillator Frequency				40	125	250	kHz
V_{RAM}	RAM Hold Voltage		During stop mode		2.0	–	–	V

NOTES:
1. V_{CC} = AV_{CC} = 4.2 to 5.5V at T_{opr} = -20 to 85 °C / -40 to 85 °C, f(XIN)=20MHz, unless otherwise specified.

Table 5.20 Electrical Characteristics (3) [Vcc = 3V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” Voltage	Except X_{OUT}	I_{OH} = -1mA		V_{CC} – 0.5	–	V_{CC}	V
		X_{OUT}	Drive capacity HIGH	I_{OH} = -0.1mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50µA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” Voltage	Except P1_0 to P1_3, X_{OUT}	I_{OL} = 1mA		–	–	0.5	V
		P1_0 to P1_3	Drive capacity HIGH	I_{OL} = 2mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1mA	–	–	0.5	V
		X_{OUT}	Drive capacity HIGH	I_{OL} = 0.1mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, CNTR0, CNTR1, TCIN, RXD0			0.2	–	0.8	V
		$\overline{RESET}$			0.2	–	1.8	V
I_{IH}	Input “H” Current		VI = 3V		–	–	4.0	µA
I_{IL}	Input “L” Current		VI = 0V		–	–	-4.0	µA
R_{PULLUP}	Pull-Up Resistance		VI = 0V		66	160	500	kΩ
R_{fXIN}	Feedback Resistance	XIN			–	3.0	–	MΩ
f_{RING-S}	Low-Speed On-Chip Oscillator Frequency				40	125	250	kHz
V_{RAM}	RAM Hold Voltage		During stop mode		2.0	–	–	V

NOTES:
1. V_{CC} = AV_{CC} = 2.7 to 3.3V at Topr = -20 to 85 °C / -40 to 85 °C, f(XIN)=10MHz, unless otherwise specified.

Rev.	Date	Description	
		Page	Summary
2.00	Jan 30, 2006	8	Figure 1.5 PRDP0020BA-A Package Pin Assignment (top view) deleted Table 1.5 Pin Description; Timer C: "CMP0_0 to CMP0_3, CMP1_0 to CMP1_3" → "CMP0_0 to CMP0_2, CMP1_0 to CMP1_2" revised
		10	Figure 2.1 CPU Register; "Reserved Area" → "Reserved Bit" revised
		12	2.8.10 Reserved Area; "Reserved Area" → "Reserved Bit" revised
		13	Figure 3.1 Memory Map of R8C/16 Group revised
		14	3.2 R8C/17 Group; (program area) → (program ROM), (data area) → (data flash) revised Figure 3.2 Memory Map of R8C/17 Group revised
		17	Table 4.3 SFR Information(3); 0085h: "Prescaler Z" → "Prescaler Z Register" 0086h: "Timer Z Secondary" → "Timer Z Secondary Register" 0087h: "Timer Z Primary" → "Timer Z Primary Register" 008Ch: "Prescaler X" → "Prescaler X Register" 008Dh: "Timer X" → "Timer X Register" 0090h, 0091h: "Timer C" → "Timer C Register" revised
		21	Table 5.4 Flash Memory (Program ROM) Electrical Characteristics; • NOTES 1 to 7 added • "Topr" → "Ambient temperature", "(Program area)" → "(Program ROM)" revised
		22	Table 5.5 Flash Memory (Data flash Block A, Block B) Electrical Characteristics; • NOTE1 revised, NOTE9 added • "Topr" → "Ambient temperature", "(Program area)" → "(Program ROM)" revised
		23	Figure 5.2 Time delay from Suspend Request until Erase Suspend revised Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics; NOTE1 revised
		24	Table 5.8 Reset Circuit Electrical Characteristics (When Using Voltage Monitor 1 Reset); NOTE2 revised Table 5.9 Reset Circuit Electrical Characteristics (When Not Using Voltage Monitor 1 Reset); NOTE1 revised
		25	Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics revised
		26	Table 5.12 Timing Requirements of I2C bus Interface (IIC); NOTE1 revised
		28	Table 5.14 Electrical Characteristics (2) [Vcc = 5V] revised
		29	"Timing Requirements (Unless ... at Ta = 25°C) [VCC = 5V]" → "Timing Requirements (Unless ... at Topr = 25°C) [VCC = 5V]" revised Table 5.18 Serial Interface; "35" → "50", "80" → "50"
		32	Table 5.21 Electrical Characteristics (4) [Vcc = 3V] revised
		33	"Timing requirements (Unless ... at Ta = 25°C) [VCC = 3V]" → "Timing requirements (Unless ... at Topr = 25°C) [VCC = 3V]" revised Table 5.25 Serial Interface; "55" → "70", "160" → "70"
		35	Package Dimensions; Package "PRDP0020BA-A" deleted

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